

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 12 A, 650 V, D2, TO-247-3L

650 V, 12 A

FFSH1265BDN-F085

Description

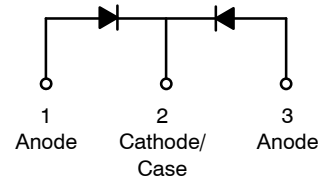
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

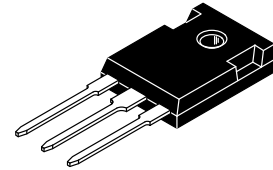
- Max Junction Temperature 175°C
- Avalanche Rated 24.5 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

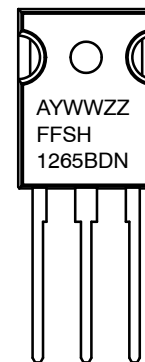


Schottky Diode



TO-247-3LD
 CASE 340CX

MARKING DIAGRAM



FFSH1265BDN	= Specific Device Code
A	= Assembly Plant Code
YWW	= Date Code (Year & Week)
G	= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSH1265BDN-F085

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	24.5*	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 145°C	6*/12**	A	
	Continuous Rectified Forward Current @ T _C < 135°C	7.2*/14.4**		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	510	A
		T _C = 150°C, 10 μs	454	A
I _{F, SM}	Non-Repetitive Forward Surge Current T _C = 25°C	Half-Sine Pulse, t _p = 8.3 ms	24	A
P _{tot}	Power Dissipation	T _C = 25°C	52	W
		T _C = 150°C	8.6	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	
	TO247 Mounting Torque, M3 Screw	60	Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

* Per Leg, ** Per Device

1. E_{AS} of 24.5 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 9.9 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max	2.9*/1.5**	°C/W

* Per Leg, ** Per Device

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted (per leg))

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 6 A, T _C = 25°C	-	1.38	1.7	V
		I _F = 6 A, T _C = 125°C	-	1.53	2.0	
		I _F = 6 A, T _C = 175°C	-	1.67	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	0.025	40	μA
		V _R = 650 V, T _C = 125°C	-	0.08	80	
		V _R = 650 V, T _C = 175°C	-	0.22	160	
Q _C	Total Capacitive Charge	V = 400 V	-	16	-	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	-	259	-	pF
		V _R = 200 V, f = 100 kHz	-	29	-	
		V _R = 400 V, f = 100 kHz	-	22	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH1265BDN-F085	FFSH1265BDN	TO-247-3LD (Pb-Free / Halogen Free)	30 Units / Tube

TYPICAL CHARACTERISTICS

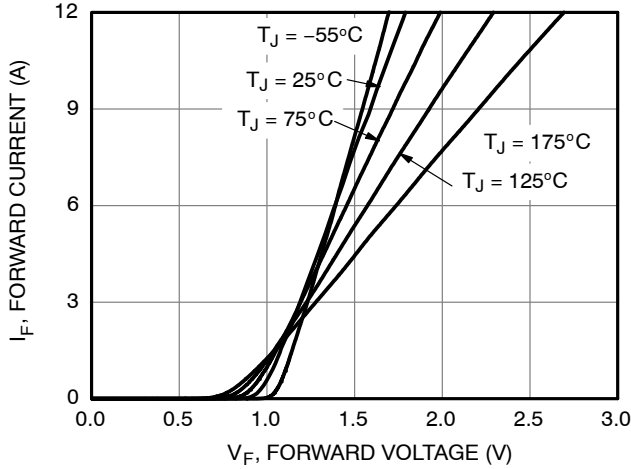


Figure 1. Forward Characteristics

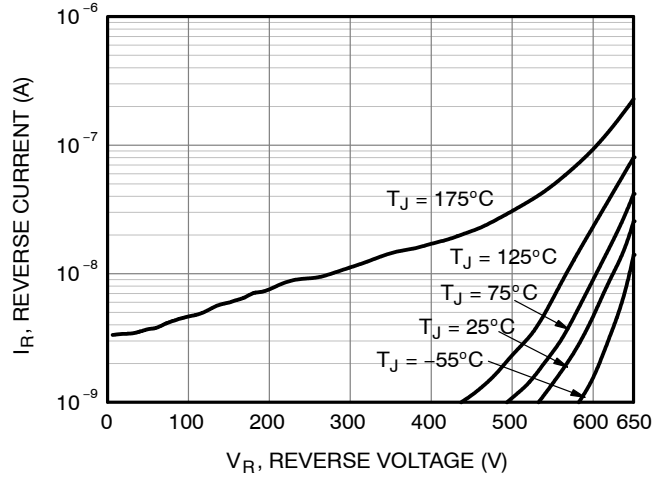


Figure 2. Reverse Characteristics

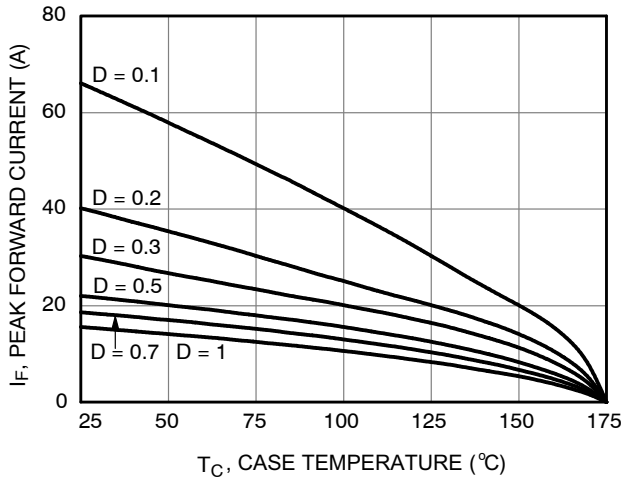


Figure 3. Current Derating

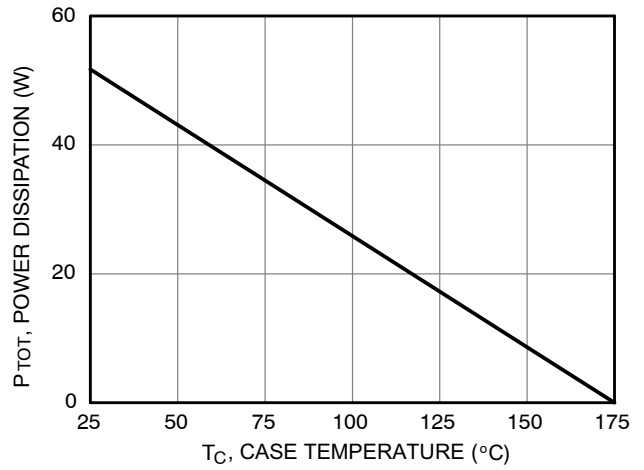


Figure 4. Power Derating

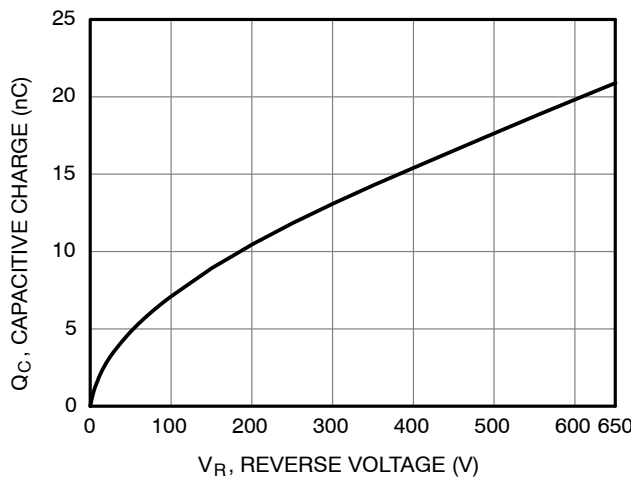


Figure 5. Capacitive Charge vs. Reverse Voltage

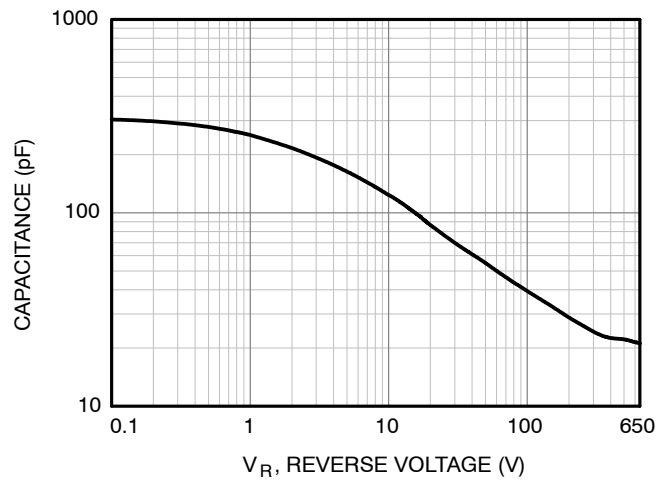


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

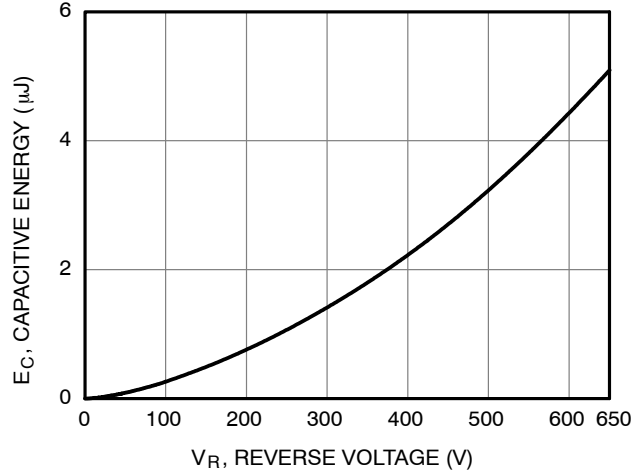


Figure 7. Capacitance Stored Energy

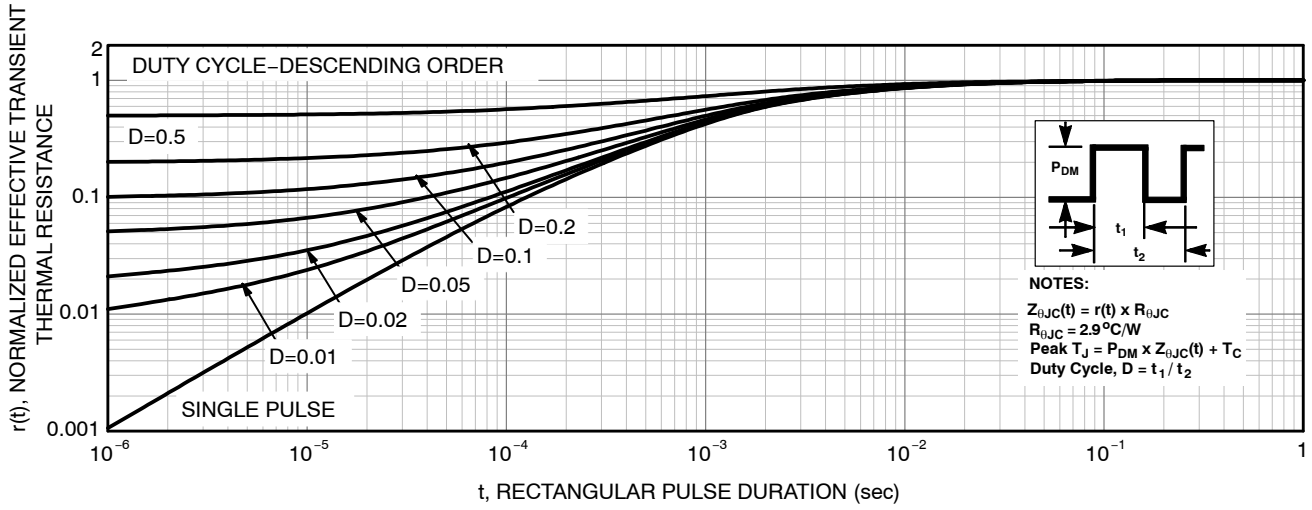


Figure 8. Junction-to-Case Transient Thermal Response

TEST CIRCUIT AND WAVEFORMS

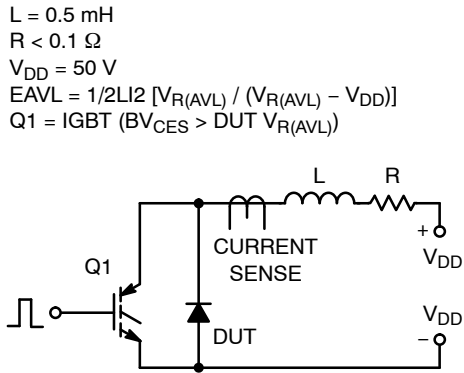


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

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